

PSMN2R0-30YLE

N-channel 30 V 2 mΩ logic level MOSFET in LPAK

12 October 2012

Product data sheet

1. Product profile

1.1 General description

Logic level N-channel MOSFET in LPAK package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

1.2 Features and benefits

- Enhanced forward biased safe operating area for superior linear mode operation
- Very low R_{DSon} for low conduction losses

1.3 Applications

- Electronic fuse
- Hot swap
- Load switch
- Soft start

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	-	30	V
I _D	drain current	T _{mb} = 25 °C; V _{GS} = 10 V; Fig. 1	[1]	-	-	100	A
P _{tot}	total power dissipation	T _{mb} = 25 °C; Fig. 2		-	-	272	W
Static characteristics							
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; Fig. 12		-	1.7	2	mΩ
		V _{GS} = 4.5 V; I _D = 25 A; T _j = 25 °C; Fig. 12		-	3	3.5	mΩ
Dynamic characteristics							
Q _{GD}	gate-drain charge	V _{GS} = 4.5 V; I _D = 25 A; V _{DS} = 15 V; Fig. 14 ; Fig. 15		-	13.8	-	nC
Q _{G(tot)}	total gate charge	V _{GS} = 10 V; I _D = 25 A; V _{DS} = 15 V; Fig. 14 ; Fig. 15		-	87	-	nC



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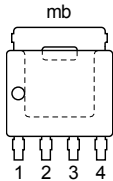
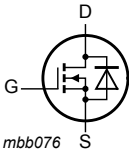


Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Avalanche ruggedness						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$V_{GS} = 10\text{ V}$; $T_{j(\text{init})} = 25\text{ °C}$; $I_D = 100\text{ A}$; $V_{\text{sup}} \leq 30\text{ V}$; unclamped; $R_{GS} = 50\text{ }\Omega$; Fig. 3	-	-	370	mJ

[1] Capped at 100A due to package

2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	 <p>LFAK; Power-SO8 (SOT669)</p>	 <p>mbb076</p>
2	S	source		
3	S	source		
4	G	gate		
mb	D	mounting base; connected to drain		

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN2R0-30YLE	LFAK; Power-SO8	plastic single-ended surface-mounted package; 4 leads	SOT669

4. Marking

Table 4. Marking codes

Type number	Marking code
PSMN2R0-30YLE	2R030

5. Limiting values

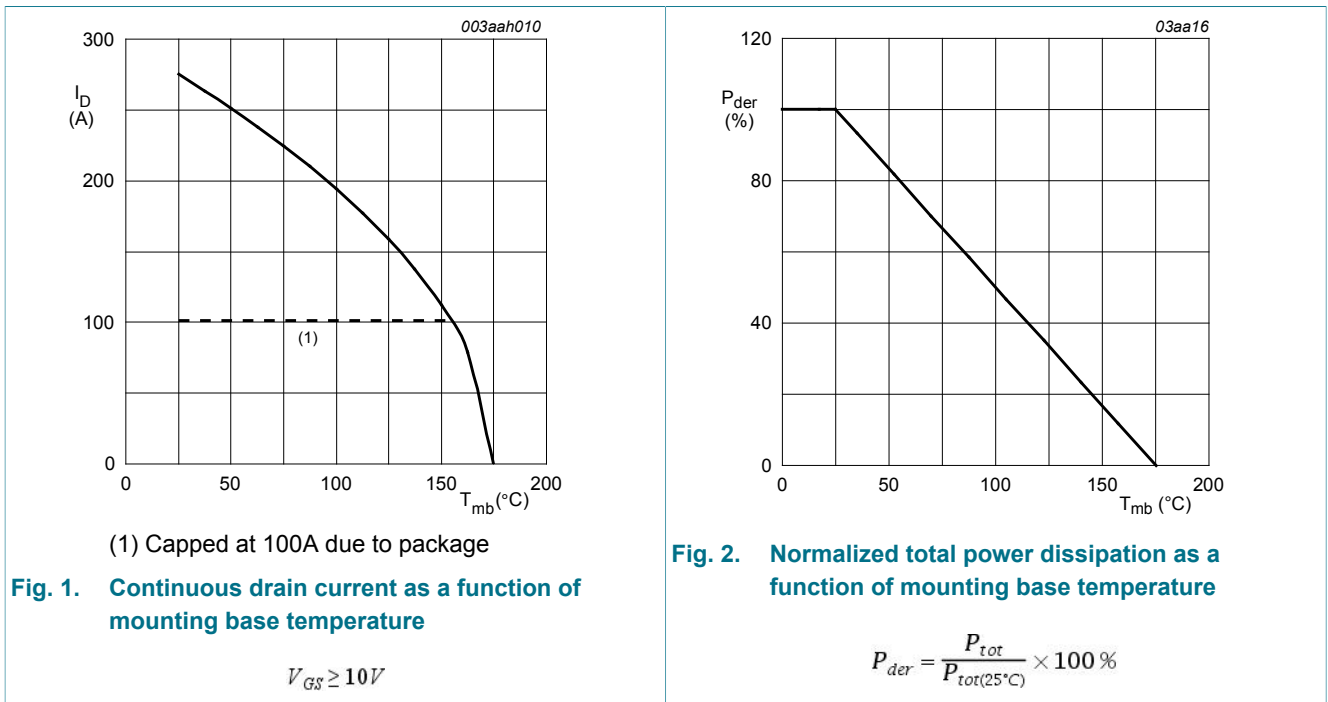
Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	$T_j \geq 25\text{ °C}$; $T_j \leq 175\text{ °C}$	-	30	V
V_{DGR}	drain-gate voltage	$T_j \leq 175\text{ °C}$; $T_j \geq 25\text{ °C}$; $R_{GS} = 20\text{ k}\Omega$	-	30	V
V_{GS}	gate-source voltage		-20	20	V

Symbol	Parameter	Conditions		Min	Max	Unit
I _D	drain current	V _{GS} = 10 V; T _{mb} = 100 °C; Fig. 1	[1]	-	100	A
		V _{GS} = 10 V; T _{mb} = 25 °C; Fig. 1	[1]	-	100	A
I _{DM}	peak drain current	pulsed; t _p ≤ 10 μs; T _{mb} = 25 °C; Fig. 4		-	1084	A
P _{tot}	total power dissipation	T _{mb} = 25 °C; Fig. 2		-	272	W
T _{stg}	storage temperature			-55	175	°C
T _j	junction temperature			-55	175	°C
T _{slid(M)}	peak soldering temperature			-	260	°C
Source-drain diode						
I _S	source current	T _{mb} = 25 °C	[1]	-	100	A
I _{SM}	peak source current	pulsed; t _p ≤ 10 μs; T _{mb} = 25 °C		-	1084	A
Avalanche ruggedness						
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V _{GS} = 10 V; T _{j(initial)} = 25 °C; I _D = 100 A; V _{sup} ≤ 30 V; unclamped; R _{GS} = 50 Ω; Fig. 3		-	370	mJ

[1] Capped at 100A due to package



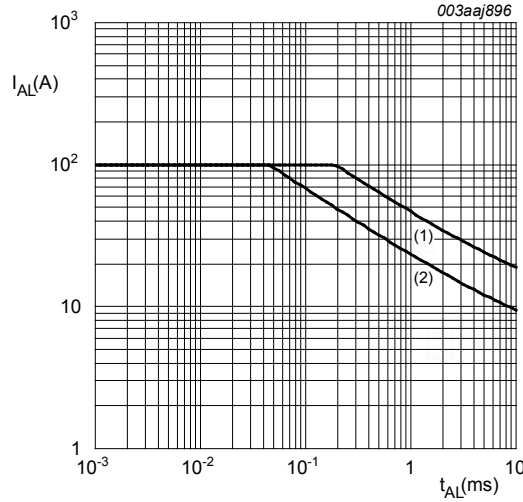


Fig. 3. Single pulse avalanche rating; avalanche current as a function of avalanche time

(1) $T_{j (init)} = 25^{\circ}C$; (2) $T_{j (init)} = 100^{\circ}C$

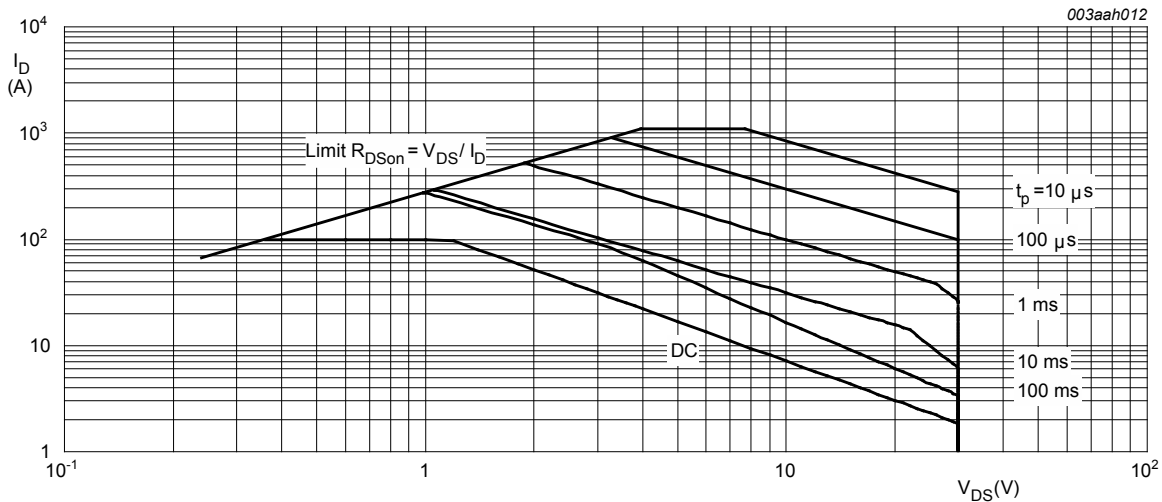


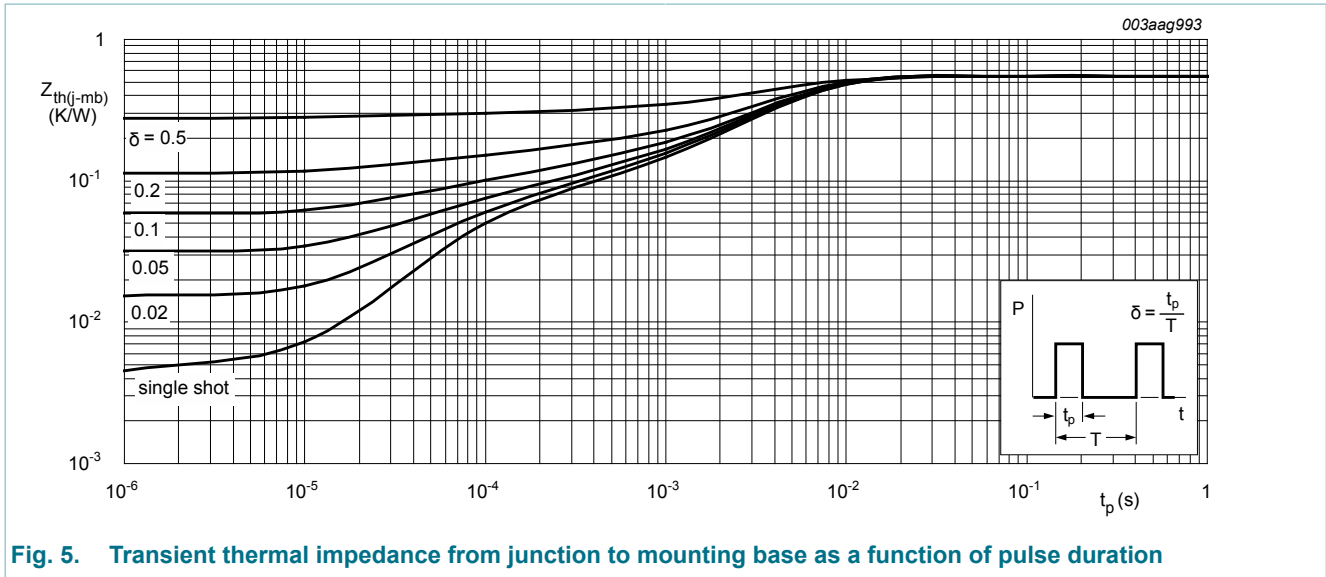
Fig. 4. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

$T_{mb} = 25^{\circ}C$; I_{DM} is a single pulse

6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	Fig. 5	-	0.45	0.55	K/W



7. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 \text{ }^\circ C$	27	-	-	V
		$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$	30	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ }^\circ C;$ Fig. 10	0.5	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ }^\circ C;$ Fig. 11; Fig. 10	1.3	1.7	2.15	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ }^\circ C;$ Fig. 10	-	-	2.45	V
I_{DSS}	drain leakage current	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ C$	-	0.05	10	μA
		$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 100 \text{ }^\circ C$	-	-	200	μA
I_{GSS}	gate leakage current	$V_{GS} = 16 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ C$	-	10	100	nA
		$V_{GS} = -16 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ C$	-	10	100	nA
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ }^\circ C;$ Fig. 12	-	1.7	2	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 100 \text{ }^\circ C;$ Fig. 13; Fig. 12	-	-	2.8	mΩ
		$V_{GS} = 4.5 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ }^\circ C;$ Fig. 12	-	3	3.5	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 175 \text{ }^\circ C;$ Fig. 13; Fig. 12	-	-	3.8	mΩ

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
R _G	internal gate resistance (AC)	f = 1 MHz	0.3	0.6	1.2	Ω
Dynamic characteristics						
Q _{G(tot)}	total gate charge	I _D = 25 A; V _{DS} = 15 V; V _{GS} = 10 V; Fig. 14 ; Fig. 15	-	87	-	nC
		I _D = 25 A; V _{DS} = 15 V; V _{GS} = 4.5 V; Fig. 14 ; Fig. 15	-	41	-	nC
		I _D = 0 A; V _{DS} = 0 V; V _{GS} = 10 V	-	79	-	nC
Q _{GS}	gate-source charge	I _D = 25 A; V _{DS} = 15 V; V _{GS} = 4.5 V; Fig. 14 ; Fig. 15	-	13.3	-	nC
Q _{GS(th)}	pre-threshold gate-source charge		-	8.1	-	nC
Q _{GS(th-pl)}	post-threshold gate-source charge		-	5.2	-	nC
Q _{GD}	gate-drain charge		-	13.8	-	nC
V _{GS(pl)}	gate-source plateau voltage	I _D = 25 A; V _{DS} = 15 V; Fig. 14 ; Fig. 15	-	2.8	-	V
C _{iss}	input capacitance	V _{DS} = 15 V; V _{GS} = 0 V; f = 1 MHz;	-	5217	-	pF
C _{oss}	output capacitance	T _j = 25 °C; Fig. 16	-	1015	-	pF
C _{rss}	reverse transfer capacitance		-	474	-	pF
t _{d(on)}	turn-on delay time	V _{DS} = 15 V; R _L = 0.6 Ω; V _{GS} = 4.5 V;	-	32.7	-	ns
t _r	rise time	R _{G(ext)} = 4.7 Ω; T _j = 25 °C	-	55.7	-	ns
t _{d(off)}	turn-off delay time		-	41.5	-	ns
t _f	fall time		-	29.5	-	ns
Source-drain diode						
V _{SD}	source-drain voltage	I _S = 25 A; V _{GS} = 0 V; T _j = 25 °C; Fig. 17	-	0.8	1.2	V
t _{rr}	reverse recovery time	I _S = 25 A; di/dt = 100 A/μs; V _{GS} = 0 V;	-	42.6	-	ns
Q _r	recovered charge	V _{DS} = 15 V	-	49.8	-	nC

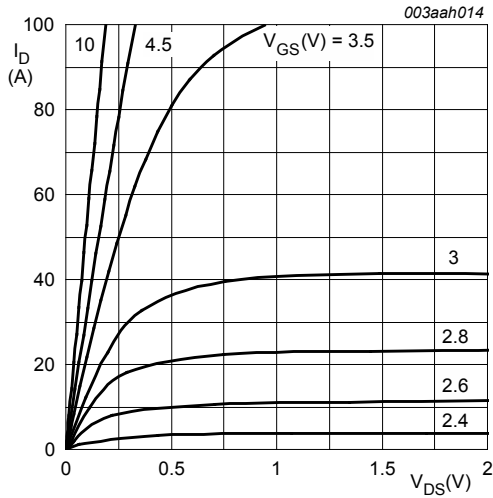


Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values

$T_j = 25^\circ\text{C}$

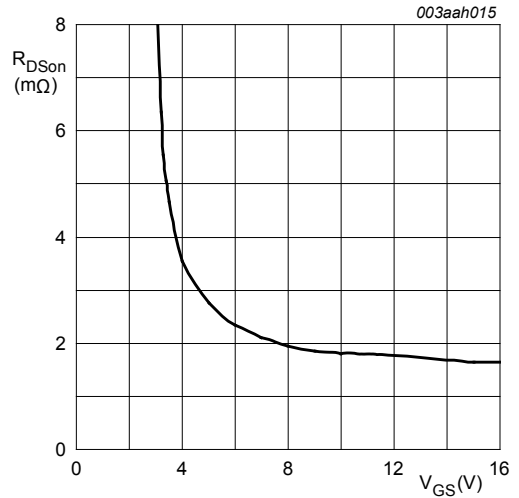


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

$T_j = 25^\circ\text{C}; I_D = 25\text{A}$

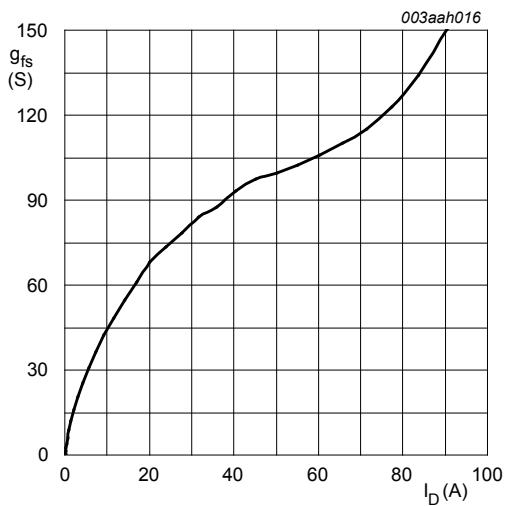


Fig. 8. Forward transconductance as a function of drain current; typical values

$T_j = 25^\circ\text{C}; V_{DS} = 10\text{V}$

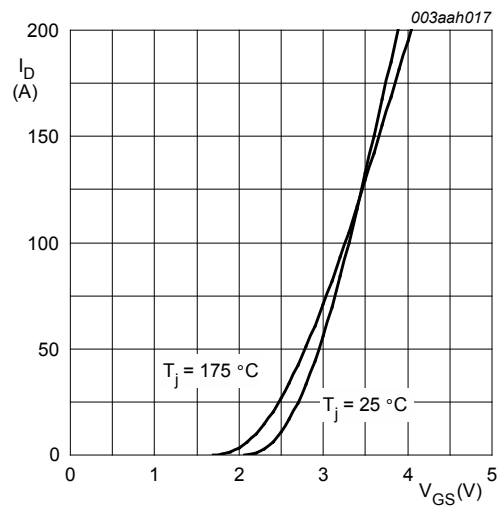


Fig. 9. Transfer characteristics; drain current as a function of gate-source voltage; typical values

$V_{DS} = 10\text{V}$

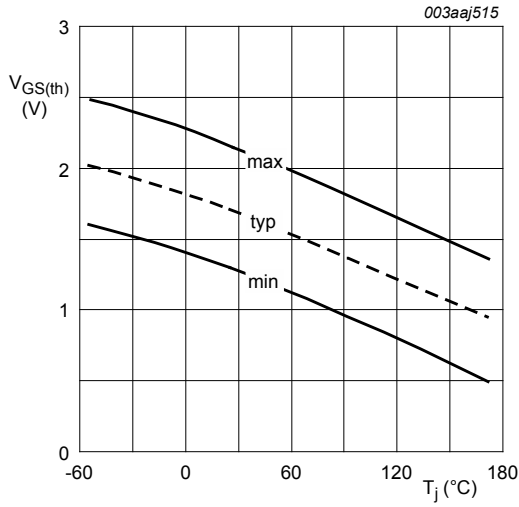


Fig. 10. Gate-source threshold voltage as a function of junction temperature

$$V_{DS} = V_{GS}$$

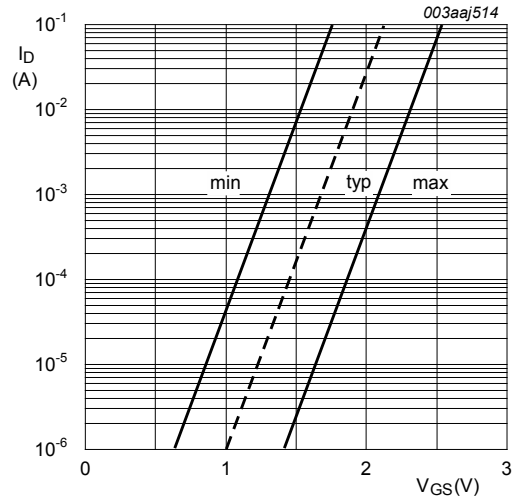


Fig. 11. Sub-threshold drain current as a function of gate-source voltage

$$T_j = 25^\circ\text{C}; V_{DS} = 5\text{V}$$

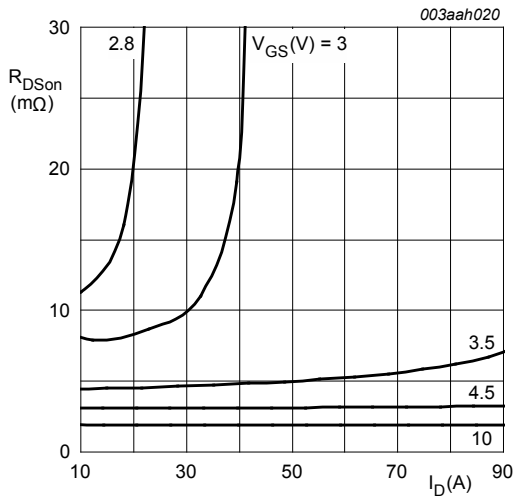


Fig. 12. Drain-source on-state resistance as a function of drain current; typical values

$$T_j = 25^\circ\text{C}$$

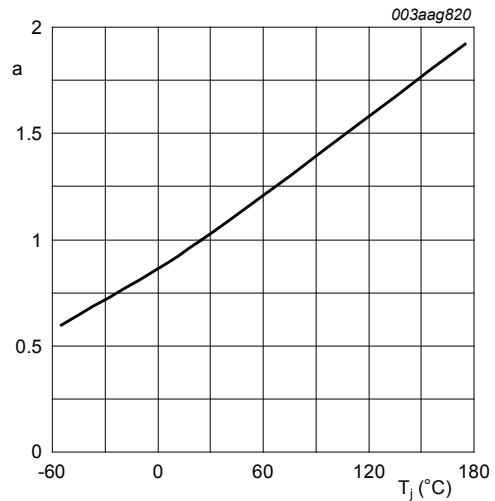


Fig. 13. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DSon}}{R_{DSon(25^\circ\text{C})}}$$

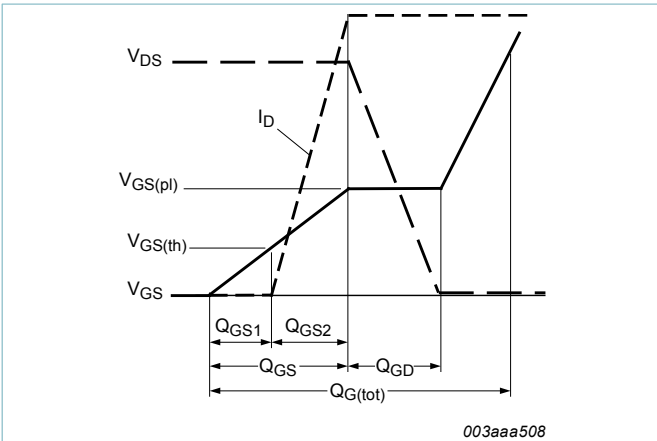


Fig. 14. Gate charge waveform definitions

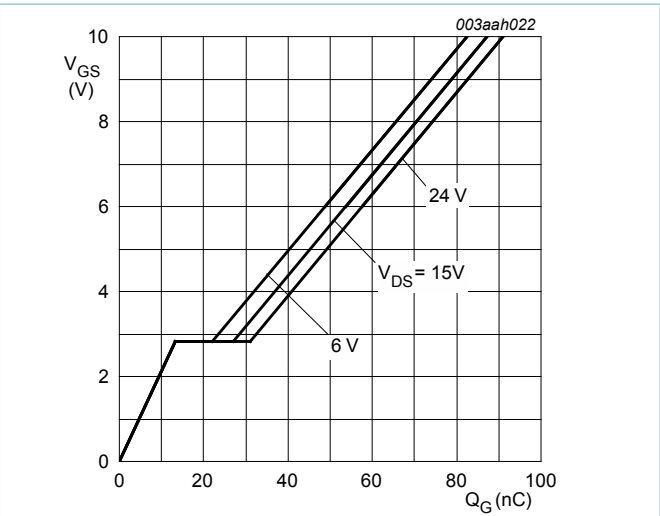


Fig. 15. Gate-source voltage as a function of gate charge; typical values

$T_j = 25^\circ C; I_D = 25A$

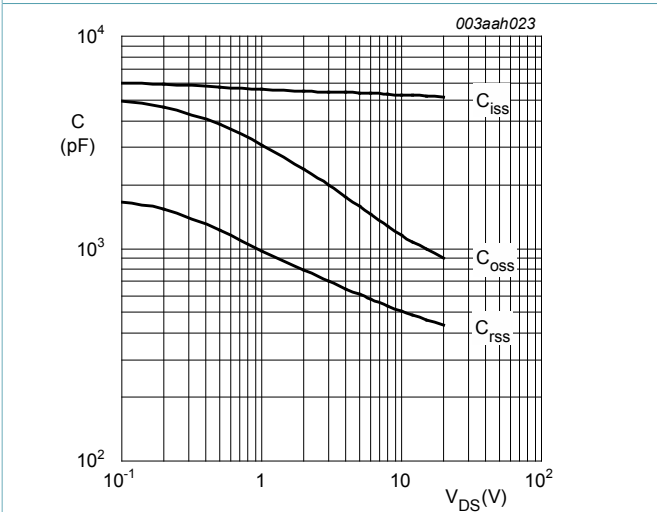


Fig. 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

$V_{GS} = 0V; f = 1MHz$

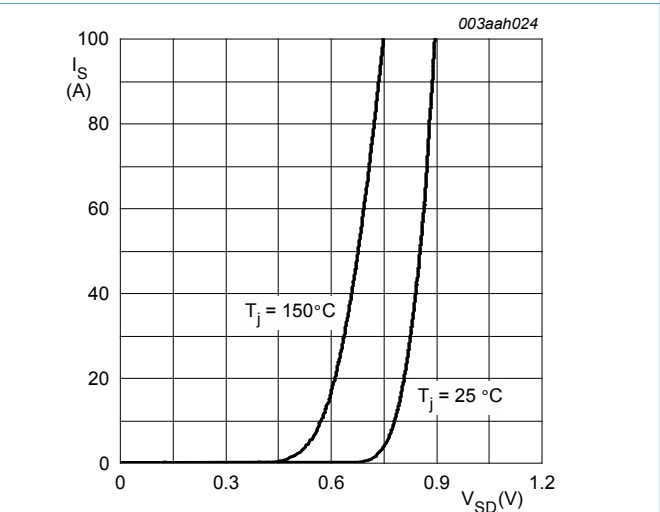


Fig. 17. Source current as a function of source-drain voltage; typical values

$V_{GS} = 0V$

8. Package outline

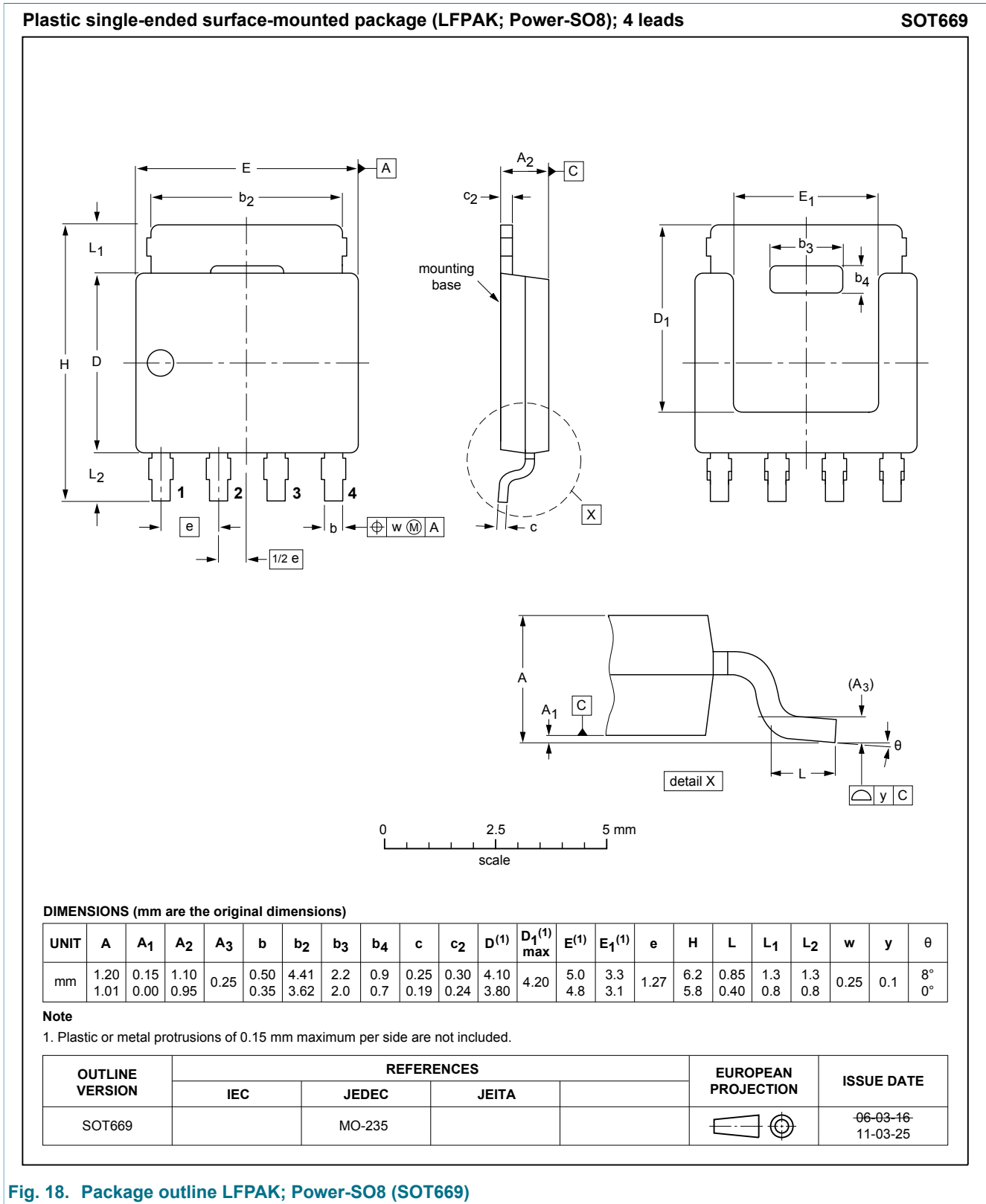


Fig. 18. Package outline LPAK; Power-SO8 (SOT669)

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9.1 Data sheet status

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